



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.
TEL: 852-2790 0314 FAX: 852-2790 0206

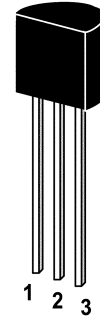
ST 2SC1623

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.

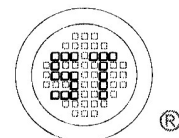


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_c	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^{\circ}\text{C}$



SEMTECH

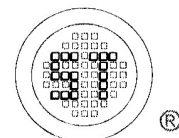
Dated : 07/12/2002

**FUKUCOM COMPANY LTD.****福 靈 有 限 公 司**FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

ST 2SC1623**Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$**

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=6\text{V}$, $I_C=1\text{mA}$					
Current Gain Group R	h_{FE}	90	-	180	-
O	h_{FE}	135	-	270	-
Y	h_{FE}	200	-	400	-
G	h_{FE}	300	-	600	-
Collector Base Breakdown Voltage at $I_C=100\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C=10\text{mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E=10\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at $V_{CB}=60\text{V}$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB}=5\text{V}$	I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage at $I_C=100\text{mA}$, $I_B=10\text{mA}$	$V_{CE(sat)}$	-	0.15	0.3	V
Base Saturation Voltage at $I_C=100\text{mA}$, $I_B=10\text{mA}$	$V_{BE(sat)}$	-	0.86	1	V
Gain Bandwidth Product at $V_{CE}=6\text{V}$, $I_C=10\text{mA}$	f_T	-	250	-	MHz
Output Capacitance at $V_{CB}=6\text{V}$, $f=1\text{MHz}$	C_{OB}	-	3	-	pF

**SEMTECH**

Dated : 07/12/2002